TOSHIBA Field-Effect Transistor Silicon P-Channel MOS Type (U-MOSVI)

SSM3J326T

Power Management Switch Applications

• 1.8-V drive

• Low ON-resistance: $R_{DS(ON)}$ = 115 m Ω (max) (@V_{GS} = -1.8 V)

 $R_{DS(ON)} = 62.5 \text{ m}\Omega \text{ (max) (@V_{GS} = -2.5 V)}$

 $R_{DS(ON)} = 45.7 \text{ m}\Omega \text{ (max) (@VGS} = -4.5 \text{ V)}$

 $R_{DS(ON)} = 39.3 \text{ m}\Omega \text{ (max) (@V_{GS} = -10 V)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-30	V(
Gate-source voltage		V _{GSS}	±12	V	
Drain current	DC	I _D (Note 1)	-5.6		
	Pulse	I _{DP} (Note 1)	-22.4		
Power dissipation		P _D (Note 2)	700	mW	
		t = 10 s	1250		
Channel temperature		T _{ch}	150	√ °C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

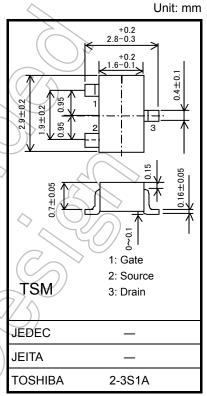
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

Precautions"/"Derating Concept and Methods") and individual reliability data

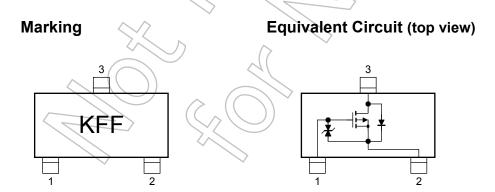
(i.e. reliability test report and estimated failure rate, etc).

Note 1: The channel temperature should not exceed 150°C during use.

Note 2: Mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm²)



Weight: 10 mg (typ.)



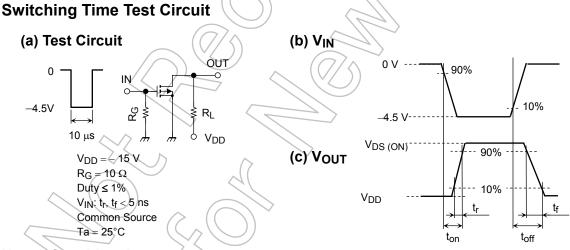
Start of commercial production 2010-01

Electrical Characteristics (Ta = 25°C)

Chara	acteristic	Symbol	Test Conditions	Min	Тур.	Max	Unit		
Drain-source breakdown voltage	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	٧			
	V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = +8 \text{ V}$ (Note 4)	-22	_	_				
Drain cut-off curre	ent	I _{DSS}	V _{DS} = -30V, V _{GS} = 0 V	_	_	-1	μА		
Gate leakage curr	ent	I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$		_	±1	μΑ		
Gate threshold vo	Itage	V _{th}	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	(-0.5	1	-1.2	V		
Forward transfer a	admittance	Y _{fs}	$V_{DS} = -3 \text{ V}, I_D = -2.5 \text{ A}$ (Note 3)	5.9	11.7	_	S		
Drain–source ON-resistance		$I_D = -4.0 \text{ A}, V_{GS} = -10 \text{ V}$ (Note 3)	/	34.2	39.3	mΩ			
	D	$I_D = -3.0 \text{ A}, V_{GS} = -4.5 \text{ V}$ (Note 3)		39.2	45.7				
	R _{DS} (ON)	$I_D = -2.5 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note 3)	> —	51	62.5				
		I _D = -1.0 A, V _{GS} = -1.8 V (Note 3)	_	67	115				
Input capacitance		C _{iss}	4(>)	_	650	1	pF		
Output capacitance		Coss	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		96	_			
Reverse transfer capacitance		C _{rss}	$(\langle // \rangle)$, –((83	_	7		
Total gate charge Gate-source charge		Qg		(4)	9.3	<i>)</i> —	nC		
		Q _{gs1}	$V_{DS} = -15 \text{ V}, I_{D} = -5.6 \text{ A}$ $V_{GS} = -4.5 \text{ V}$	7-	1.65				
Gate-drain charge		Q _{gd}	VGS - 719V	(A)	3.1	_			
Switching time	Turn-on time	t _{on}	$V_{DD} = -15 \text{ V}, I_D = -2.0 \text{ A},$	\ <u></u>	15	_	ns		
	Turn-off time	t _{off}	$V_{GS} = 0 \text{ to } -4.5 \text{ V}, R_G = 10 \Omega$))—	92	_			
Drain-source forw	ard voltage	V _{DSF}	$I_D = 5.6 \text{ A, V}_{GS} = 0 \text{ V}$ (Note 3)	_	0.9	1.2	V		

Note3: Pulse test

Note4: If a forward bias is applied between gate and source, this device enters V(BR)DSX mode. Note that the drain-source breakdown voltage is lowered in this mode.



Usage Considerations

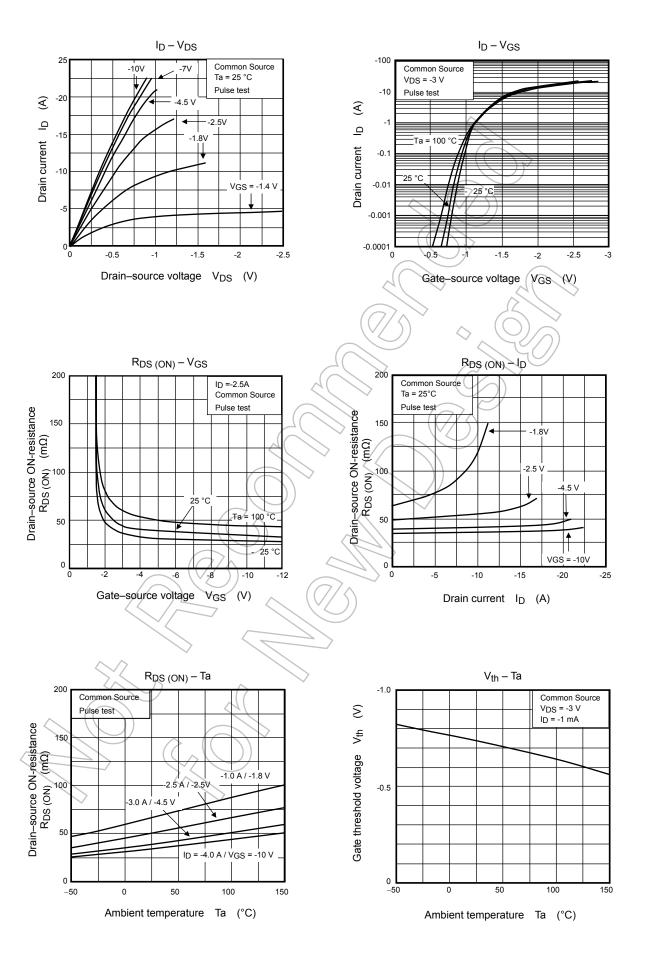
Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below –1 mA for the SSM3J326T. Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$.

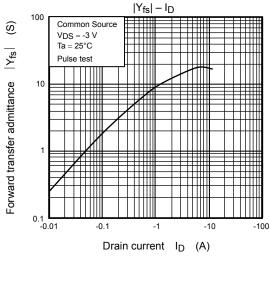
Take this into consideration when using the device.

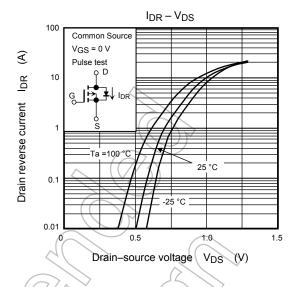
Handling Precaution

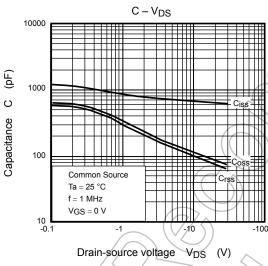
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

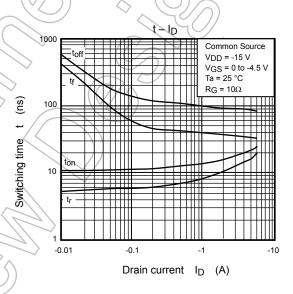
Thermal resistance $R_{th\ (ch-a)}$ and power dissipation P_D vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration.

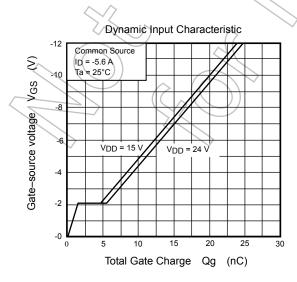




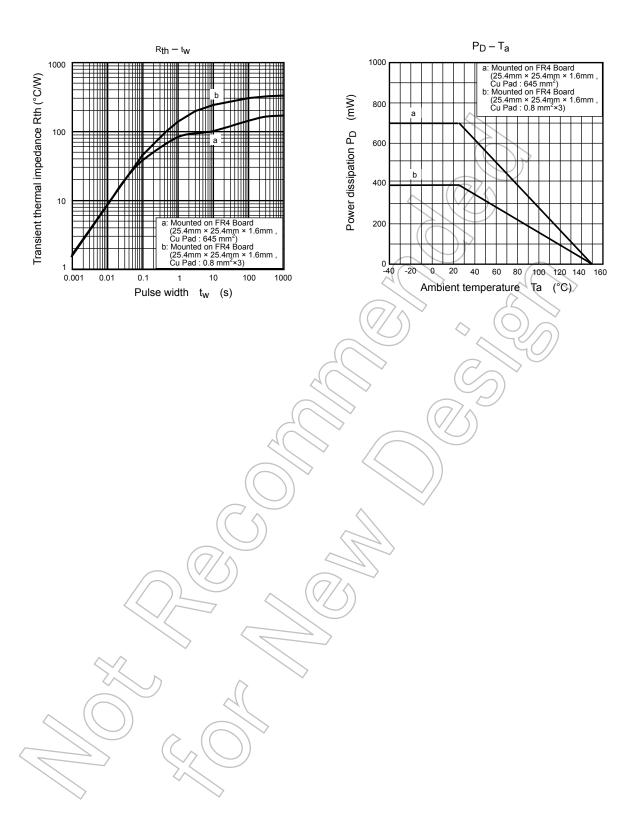








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